

P-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
- 100	0.026at V _{GS} = - 10 V	- 48	15 nC
	0.029 at V _{GS} = - 4.5 V		

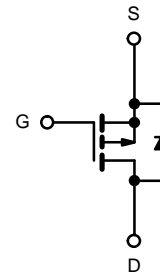
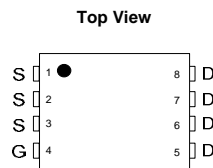
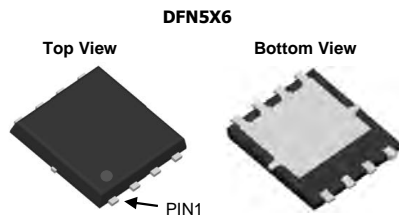
FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested



APPLICATIONS

- Notebook
- Load Switch



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	- 100	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	- 48 ^a
		T _C = 70 °C	- 35 ^a
		T _A = 25 °C	- 9 ^{b, c}
		T _A = 70 °C	- 5.3 ^{b, c}
Pulsed Drain Current	I _{DM}	- 192	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	- 8.8 ^{b, c}
Single Pulse Avalanche Current	I _{AS}	-48	mJ
Single Pulse Avalanche Energy	E _{AS}	56	
Maximum Power Dissipation	P _D	T _C = 25 °C	156
		T _C = 70 °C	113
		T _A = 25 °C	6.6 ^{b, c}
		T _A = 70 °C	1.7 ^{b, c}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	t ≤ 10 s	R _{thJA}	19	40	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	1.0	2.0	

Notes:

- Package limited.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- The DFN5x6 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under Steady State conditions is 54 °C/W.

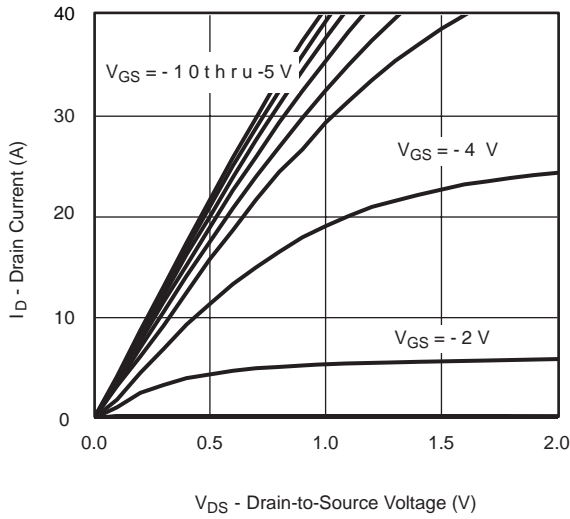
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-100			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		-31		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		6.5			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1.0		-3.0	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -80\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -80\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	-48			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -15\text{ A}$		0.026	0.035	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -10\text{ A}$		0.029	0.040	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -15\text{ A}$		52		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -80\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		6950		pF
Output Capacitance	C_{oss}		775			
Reverse Transfer Capacitance	C_{rss}		215			
Total Gate Charge	Q_g	$V_{DS} = -80\text{ V}, V_{GS} = -10\text{ V}, I_D = -15\text{ A}$		15		nC
		$V_{DS} = -80\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -10\text{ A}$		12		
Gate-Source Charge	Q_{gs}	$V_{DS} = -80\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -10\text{ A}$		20		
Gate-Drain Charge	Q_{gd}			32		
Gate Resistance	R_g	$f = 1\text{ MHz}$		1.1		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = -80\text{ V}, R_L = 15\text{ }\Omega$ $I_D \equiv -10\text{ A}, V_{GS} = -10\text{ V}, R_g = 1\text{ }\Omega$		15		ns
Rise Time	t_r		32			
Turn-Off Delay Time	$t_{d(off)}$		27			
Fall Time	t_f		20			
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = -80\text{ V}, R_L = 15\text{ }\Omega$ $I_D \equiv -10\text{ A}, V_{GS} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		19		
Rise Time	t_r		45			
Turn-Off Delay Time	$t_{d(off)}$		35			
Fall Time	t_f		23			
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			-48	A
Pulse Diode Forward Current ^a	I_{SM}				-192	
Body Diode Voltage	V_{SD}	$I_S = -10\text{ A}$		-0.7	-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		30		ns
Body Diode Reverse Recovery Charge	Q_{rr}		35		nC	
Reverse Recovery Fall Time	t_a		16		ns	
Reverse Recovery Rise Time	t_b		14			

Notes:

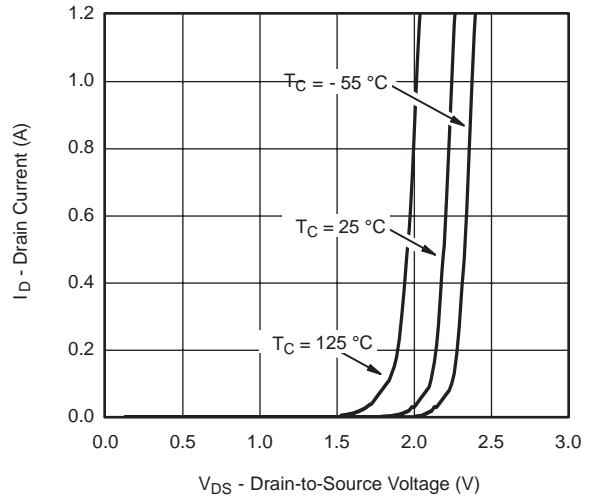
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

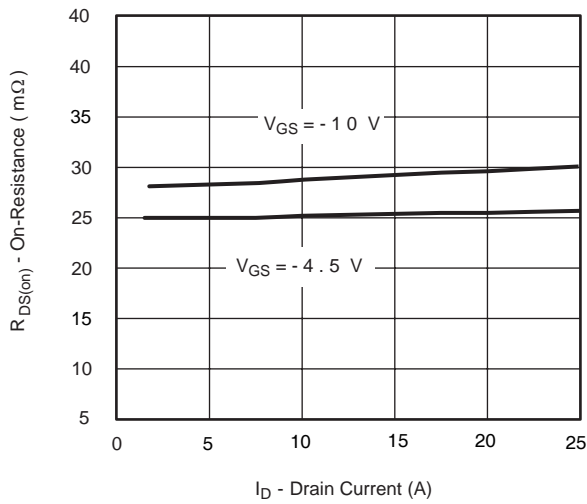
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



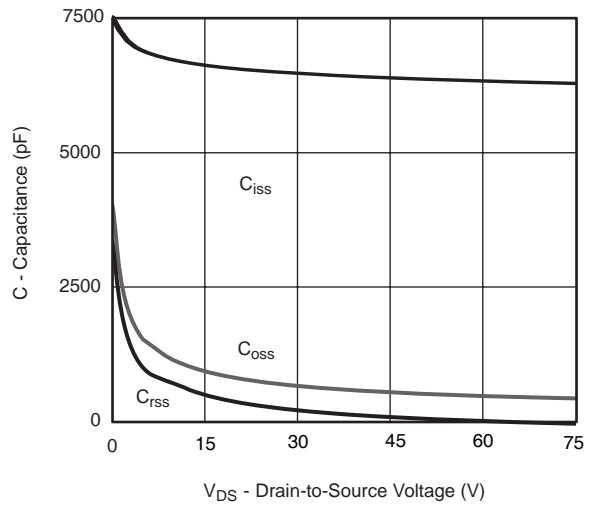
V_{DS} - Drain-to-Source Voltage (V)
Output Characteristics



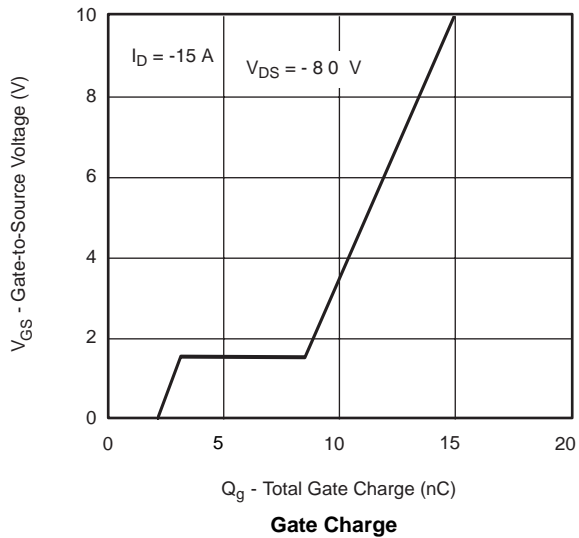
V_{DS} - Drain-to-Source Voltage (V)
Transfer Characteristics



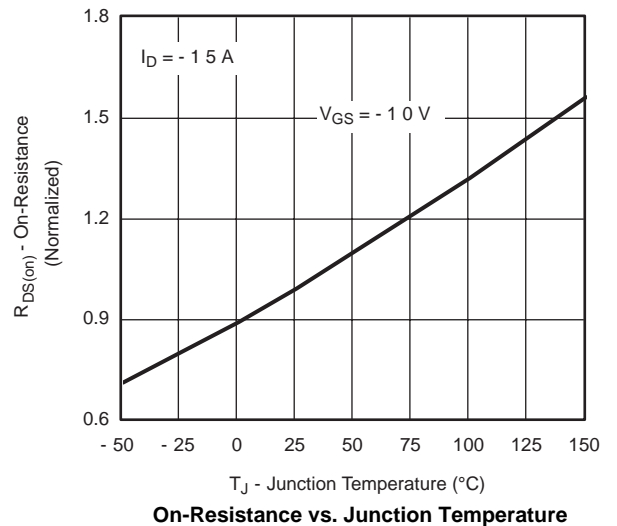
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

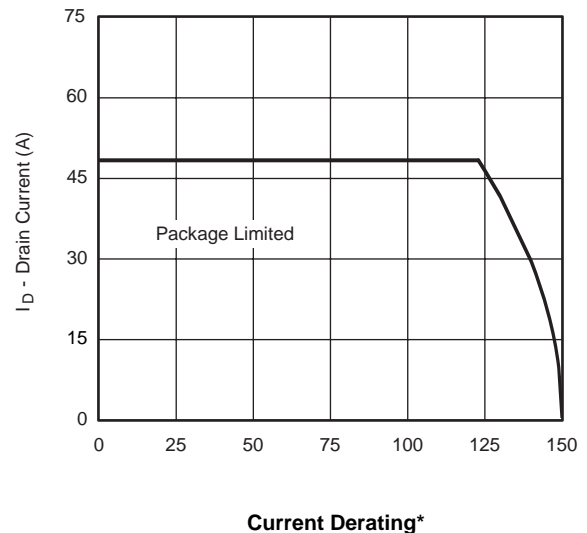
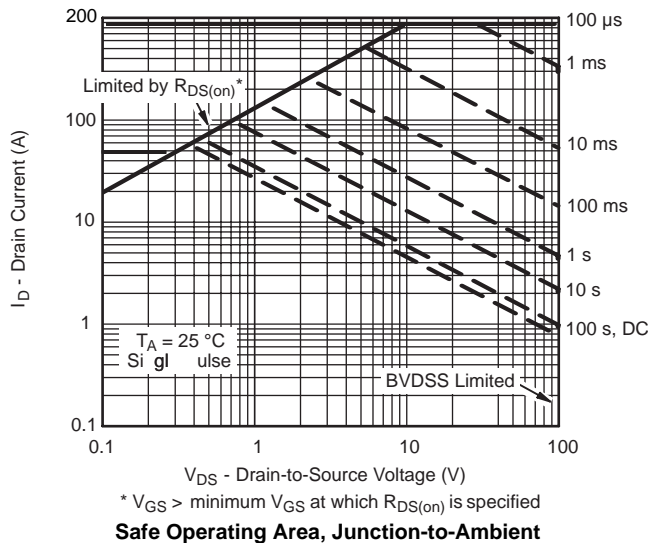
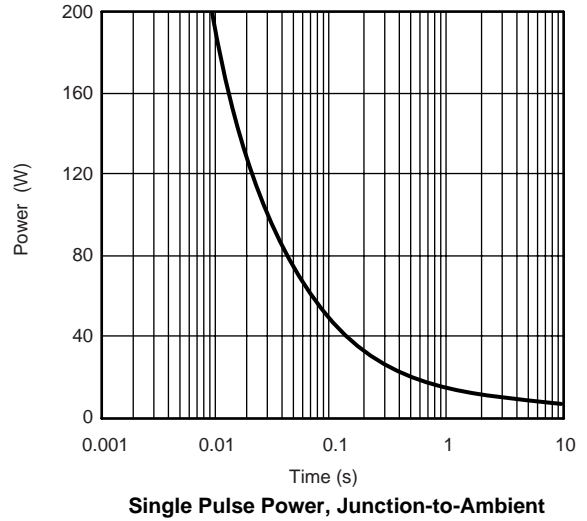
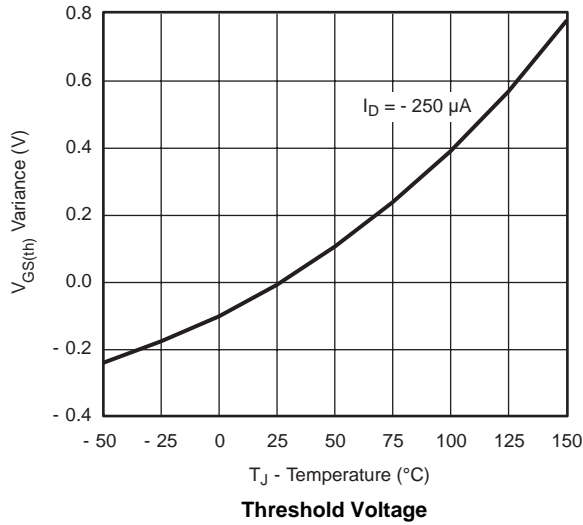
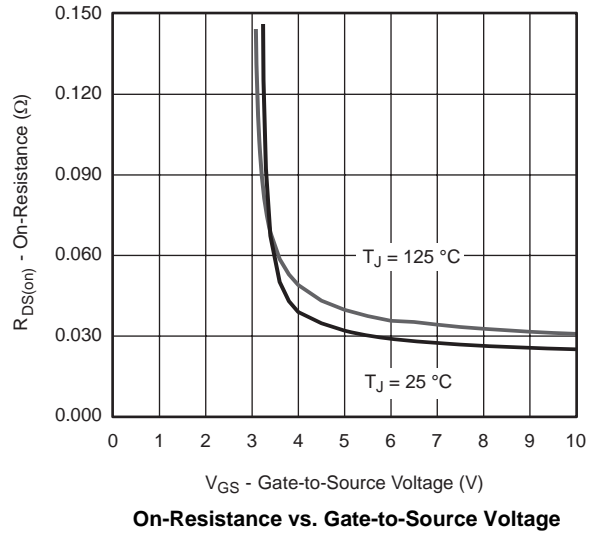
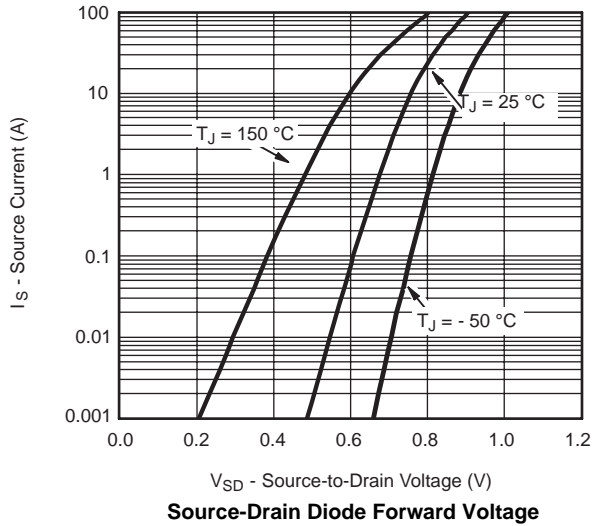


Gate Charge

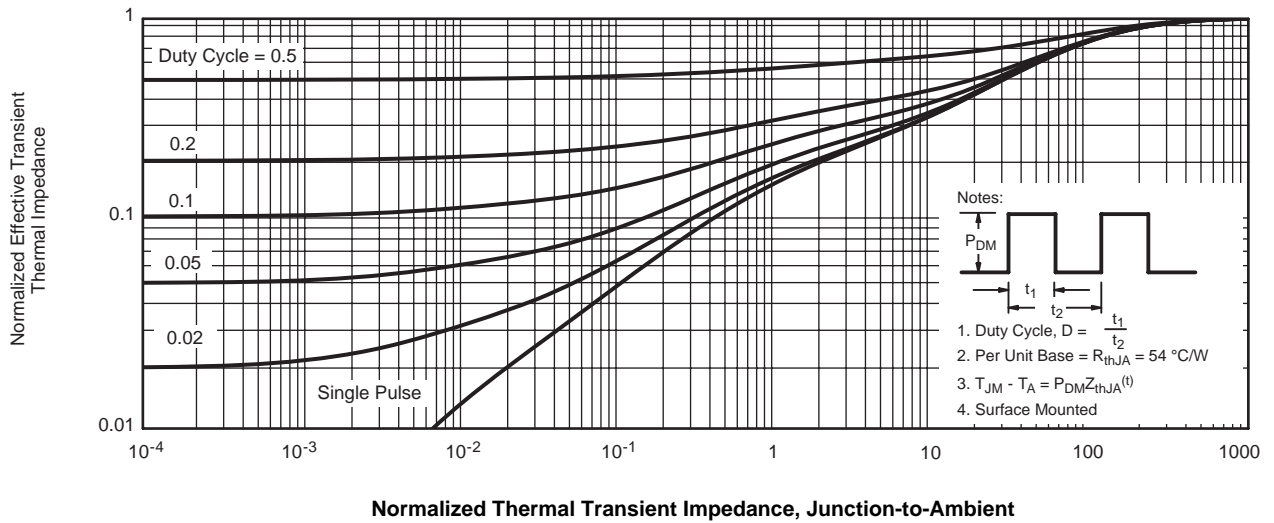


On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

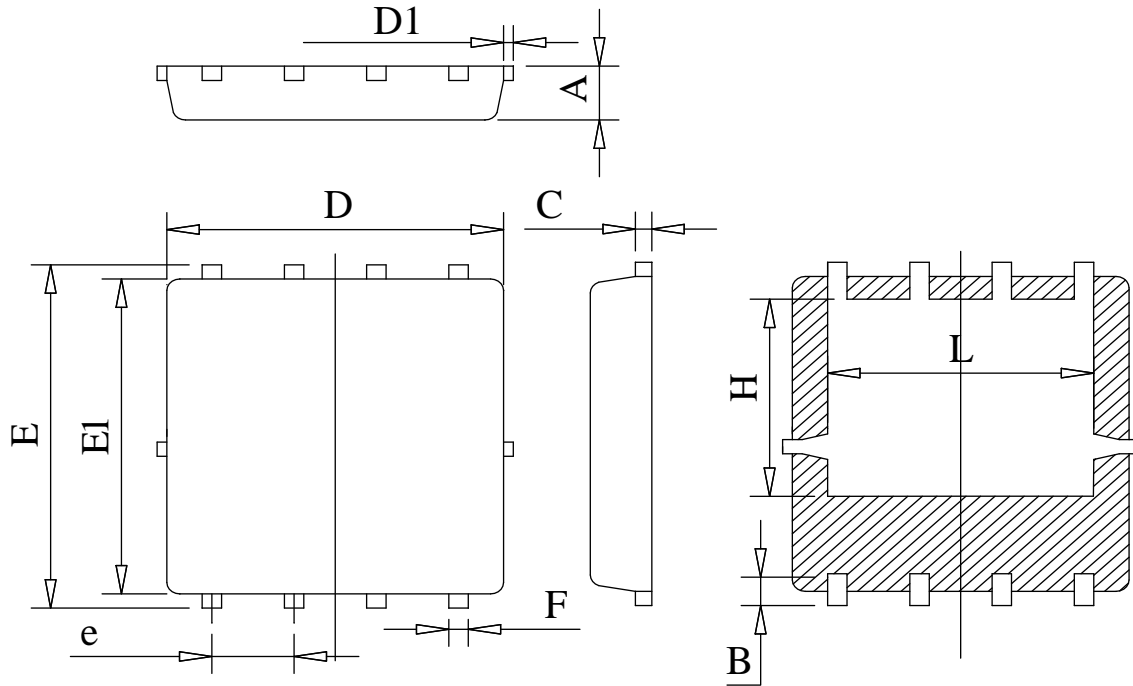


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on T_{J(max)} = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

DFN5X6-8L PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

Unit : mm

Symbol	Min	Typ	Max
A	0.78	0.95	1.12
B	0.45	0.58	0.78
C	0.18	0.254	0.36
D	4.70	5.20	5.45
D1			0.18
E	5.85	6.05	6.25
E1	5.38	5.55	5.98
e	1.15	1.27	1.40
F	0.18	0.30	0.52
H	3.25	3.47	3.70
L	3.75	4.00	4.25

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